Preferred Device

Dual Bias Resistor Transistors

NPN Silicon Surface Mount Transistors with Monolithic Bias Resistor Network

The BRT (Bias Resistor Transistor) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. These digital transistors are designed to replace a single device and its external resistor bias network. The BRT eliminates these individual components by integrating them into a single device. In the NSB1011XV6T5, two BRT devices are housed in the SOT-563 package which is ideal for low power surface mount applications where board space is at a premium.

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- This device is manufactured with a Pb-Free external lead finish only.

MAXIMUM RATINGS

 $(T_A = 25^{\circ}C \text{ unless otherwise noted, common for } Q_1 \text{ and } Q_2)$

Rating	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	50	Vdc
Collector-Emitter Voltage	V _{CEO}	50	Vdc
Collector Current	Ι _C	100	mAdc

THERMAL CHARACTERISTICS

Characteristic (One Junction Heated)	Symbol	Мах	Unit
Total Device Dissipation T _A = 25°C Derate above 25°C	P _D	357 (Note 1) 2.9 (Note 1)	mW mW/°C
Thermal Resistance – Junction-to-Ambient	$R_{\theta JA}$	350 (Note 1)	°C/W
Characteristic (Both Junctions Heated)	Symbol	Max	Unit
			Onit
Total Device Dissipation T _A = 25°C Derate above 25°C	P _D	500 (Note 1) 4.0 (Note 1)	mW mW/°C
Total Device Dissipation T _A = 25°C Derate above 25°C Thermal Resistance – Junction-to-Ambient	P _D R _{θJA}	500 (Note 1) 4.0 (Note 1) 250 (Note 1)	mW mW/°C °C/W

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. FR-4 @ Minimum Pad.



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SOT-563 CASE 463A PLASTIC

MARKING DIAGRAM



UT = Specific Device Code

(see table on following page)

D = Date Code

ORDERING INFORMATION

Device	Package	Shipping [†]
NSB1011XV6T5	SOT-563 (Pb-Free)	8000 / Tape & Reel

⁺For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
Q1 OFF CHARACTERISTICS					
Collector-Base Cutoff Current (V _{CB} = 50 V, I_E = 0)	I _{CBO}	-	-	100	nAdc
Collector-Emitter Cutoff Current (V _{CE} = 50 V, I_B = 0)	I _{CEO}	-	-	500	nAdc
Emitter-Base Cutoff Current (V_{EB} = 6.0 V, I_C = 0)	I _{EBO}	-	-	0.5	mAdc
Collector-Base Breakdown Voltage (I _C = 10 μ A, I _E = 0)	V _{(BR)CBO}	50	-	-	Vdc
Collector-Emitter Breakdown Voltage (Note 2) (I_{C} = 2.0 mA, I_{B} = 0)	V _{(BR)CEO}	50	-	_	Vdc
ON CHARACTERISTICS (Note 2)					
DC Current Gain (V_{CE} = 10 V, I_C = 5.0 mA)	h _{FE}	35	60	-	-
Collector-Emitter Saturation Voltage ($I_C = 10 \text{ mA}, I_B = 0.3 \text{ mA}$)	V _{CE(sat)}	-	-	0.25	Vdc
Output Voltage (on) (V _{CC} = 5.0 V, V _B = 2.5 V, R _L = 1.0 k Ω)	V _{OL}	-	-	0.2	Vdc
Output Voltage (off) (V _{CC} = 5.0 V, V _B = 0.5 V, R _L = 1.0 k Ω)	V _{OH}	4.9	-	-	Vdc
Input Resistor	R1	7.0	10	13	kΩ
Resistor Ratio	R1/R2	0.8	1.0	1.2	-
Q2 OFF CHARACTERISTICS					
Collector-Base Cutoff Current ($V_{CB} = 50 \text{ V}, I_E = 0$)	I _{CBO}	-	-	100	nAdc
Collector-Emitter Cutoff Current (V_{CE} = 50 V, I_B = 0)	I _{CEO}	-	-	500	nAdc
Emitter-Base Cutoff Current (V_{EB} = 6.0 V, I_C = 0)	I _{EBO}	-	-	0.2	mAdc
Collector-Base Breakdown Voltage ($I_C = 10 \ \mu A, I_E = 0$)	V _{(BR)CBO}	50	-	-	Vdc
Collector-Emitter Breakdown Voltage (Note 2) (I_{C} = 2.0 mA, I_{B} = 0)	V _{(BR)CEO}	50	-	_	Vdc
ON CHARACTERISTICS (Note 2)					
DC Current Gain (V_{CE} = 10 V, I_C = 5.0 mA)	h _{FE}	80	140	-	-
Collector-Emitter Saturation Voltage ($I_C = 10 \text{ mA}, I_B = 0.3 \text{ mA}$)	V _{CE(sat)}	-	-	0.25	Vdc
Output Voltage (on) (V _{CC} = 5.0 V, V _B = 2.5 V, R _L = 1.0 k Ω)	V _{OL}	-	-	0.2	Vdc
Output Voltage (off) (V_{CC} = 5.0 V, V_B = 0.5 V, R_L = 1.0 k\Omega)	V _{OH}	4.9	-	_	Vdc
Input Resistor	R1	1.54	2.2	2.86	kΩ
Resistor Ratio	R1/R2	0.038	0.047	0.056	-

2. Pulse Test: Pulse Width < 300 $\mu s,$ Duty Cycle < 2.0%.



Figure 1. Derating Curve

TYPICAL ELECTRICAL CHARACTERISTICS - Q1



0.1 ∟ 0 20 10 30 40 50 IC, COLLECTOR CURRENT (mA)

Figure 6. Input Voltage versus Output Current

TYPICAL ELECTRICAL CHARACTERISTICS - Q2



Figure 11. Input Voltage versus Output Current

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



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01 2 3			8 0.13	0.18	
		J 1.5	0 1.60	1.70	
	c	E 1.10		1.30	
		н 15		1.70	
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5. ANDDE 5. DRAIN 5. GATE 2 6. CATHODE 6. DRAIN 6. DRAIN	2	XX = Specific M = Month (Device Code		
STYLE 10: STYLE 11:		■ = Pb–Fre	e Package		
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SOT-563-6 1.60x1.20x0.55, 0.50P

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